

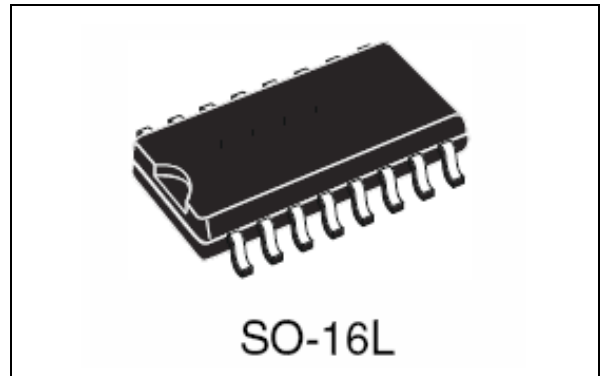
Double channel high-side driver

Features

Type	$R_{DS(on)}$	I_{OUT}	V_{CC}
VND830P-E	60 m $\Omega^{(1)}$	6 A ⁽¹⁾	36 V

1. Per each channel.

- ECOPACK®: lead free and RoHS compliant
- Automotive Grade: compliance with AEC guidelines
- Very low standby current
- CMOS compatible input
- On-state open-load detection
- Off-state open-load detection
- Thermal shutdown protection and diagnosis
- Undervoltage shutdown
- Overvoltage clamp
- Output stuck to V_{CC} detection
- Load current limitation
- Reverse battery protection
- Electrostatic discharge protection



Description

The VND830P-E is a monolithic device made by using STMicroelectronics™ VIPower™ M0-3 technology, intended for driving any kind of load with one side connected to ground.

Active V_{CC} pin voltage clamp protects the devices against low energy spikes (see ISO7637 transient compatibility table).

Active current limitation combined with thermal shutdown and automatic restart protects the device against overload. The device detects open-load condition both in on-state and off-state. Output shorted to V_{CC} is detected in the off-state. Device automatically turns-off in case of ground pin disconnection.

Table 1. Device summary

Package	Order codes	
	Tube	Tape and reel
SO-16L	VND830P-E	VND830PTR-E

Contents

1	Block diagram and pin description	5
2	Electrical specifications	6
2.1	Absolute maximum ratings	6
2.2	Thermal data	7
2.3	Electrical characteristics	7
2.4	Electrical characteristics curves	13
3	Application information	16
3.1	GND protection network against reverse battery	16
3.1.1	Solution 1: a resistor in the ground line (RGND only)	16
3.1.2	Solution 2: a diode (D _{GND}) in the ground line	17
3.2	Load dump protection	17
3.3	MCU I/O protection	17
3.4	Open-load detection in off-state	18
3.5	Maximum demagnetization energy	19
4	Package and PCB thermal data	20
4.1	SO-16L thermal data	20
5	Package and packing information	23
5.1	ECOPACK® packages	23
5.2	SO-16L package information	23
5.3	SO-16L packing information	25
6	Revision history	26

List of tables

Table 1.	Device summary	1
Table 2.	Suggested connections for unused and not connected pins	5
Table 3.	Absolute maximum ratings	6
Table 4.	Thermal data (per island)	7
Table 5.	Power output.	7
Table 6.	Protections	8
Table 7.	V _{CC} - output diode	8
Table 8.	Status pin	8
Table 9.	Switching (V _{CC} = 13 V)	9
Table 10.	Open-load detection	9
Table 11.	Logic input	9
Table 12.	Truth table.	10
Table 13.	Electrical transient requirements on V _{CC} pin (part 1)	11
Table 14.	Electrical transient requirements on V _{CC} pin (part 2)	11
Table 15.	Electrical transient requirements on V _{CC} pin (part 3)	11
Table 16.	Thermal parameters	22
Table 17.	SO-16L mechanical data	24
Table 18.	Document revision history	26

List of figures

Figure 1.	Block diagram	5
Figure 2.	Configuration diagram (top view)	5
Figure 3.	Current and voltage conventions	7
Figure 4.	Switching time waveforms	10
Figure 5.	Waveforms	12
Figure 6.	Off-state output current	13
Figure 7.	High level input current	13
Figure 8.	Input clamp voltage	13
Figure 9.	Status leakage current	13
Figure 10.	Status low output voltage	13
Figure 11.	Status clamp voltage	13
Figure 12.	Overvoltage shutdown	14
Figure 13.	I_{LIM} vs T_{case}	14
Figure 14.	Turn-on voltage slope	14
Figure 15.	Turn-off voltage slope	14
Figure 16.	On-state resistance vs T_{case}	14
Figure 17.	On-state resistance vs V_{CC}	14
Figure 18.	Input high level	15
Figure 19.	Input low level	15
Figure 20.	Open-load on-state detection threshold	15
Figure 21.	Open-load off-state detection threshold	15
Figure 22.	Input hysteresis voltage	15
Figure 23.	Application schematic	16
Figure 24.	Open-load detection in off-state	18
Figure 25.	SO-16L maximum turn-off current versus load inductance	19
Figure 26.	SO-16L PC board	20
Figure 27.	$R_{thj-amb}$ vs PCB copper area in open box free air condition	20
Figure 28.	SO-16 L thermal impedance junction ambient single pulse	21
Figure 29.	Thermal fitting model of a quad channel HSD in SO-16L	21
Figure 30.	SO-16L package dimensions	23
Figure 31.	SO-16L tube shipment (no suffix)	25
Figure 32.	Tape and reel shipment (suffix "TR")	25

1 Block diagram and pin description

Figure 1. Block diagram

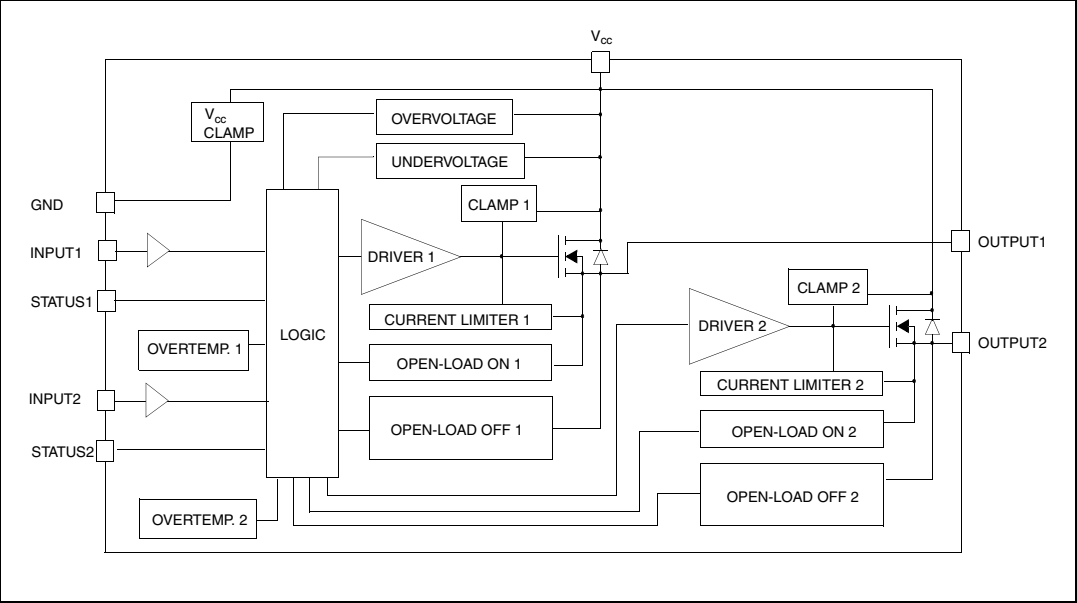


Figure 2. Configuration diagram (top view)

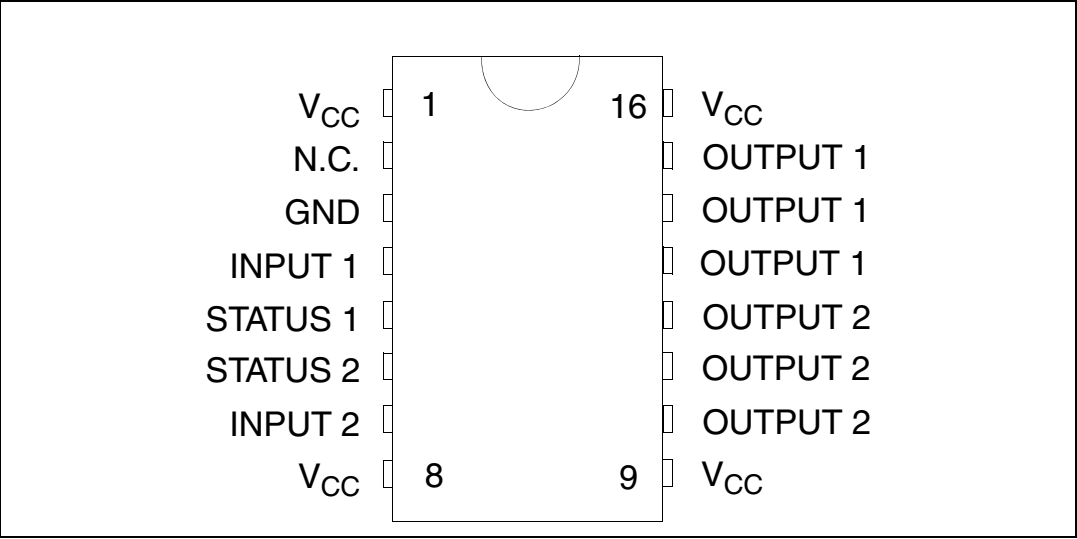


Table 2. Suggested connections for unused and not connected pins

Connection / pin	Status	N.C.	Output	Input
Floating	X	X	X	X
To ground	-	X	-	Through 10 KΩ resistor

2 Electrical specifications

2.1 Absolute maximum ratings

Stressing the device above the rating listed in [Table 3](#) may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the operating sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Refer also to the STMicroelectronics SURE Program and other relevant quality document.

Table 3. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CC}	DC supply voltage	41	V
$-V_{CC}$	Reverse DC supply voltage	- 0.3	V
$-I_{GND}$	DC reverse ground pin current	- 200	mA
I_{OUT}	DC output current	Internally limited	A
$-I_{OUT}$	Reverse DC output current	- 6	A
I_{IN}	DC input current	+/- 10	mA
I_{STAT}	DC status current	+/- 10	mA
V_{ESD}	Electrostatic discharge (Human Body Model: $R=1.5\text{ K}\Omega$; $C=100\text{ pF}$)		
	- INPUT	4000	V
	- STATUS	4000	V
	- OUTPUT	5000	V
	- V_{CC}	5000	V
E_{MAX}	Maximum switching energy ($L=1.8\text{ mH}$; $R_L=0\text{ }\Omega$; $V_{bat}=13.5\text{ V}$; $T_{jstart}=150\text{ }^\circ\text{C}$; $I_L=9\text{ A}$)	102	mJ
P_{tot}	Power dissipation $T_{lead}=25\text{ }^\circ\text{C}$	8.3	W
T_j	Junction operating temperature	Internally limited	$^\circ\text{C}$
T_c	Case operating temperature	- 40 to 150	$^\circ\text{C}$
T_{stg}	Storage temperature	- 55 to 150	$^\circ\text{C}$

2.2 Thermal data

Table 4. Thermal data (per island)

Symbol	Parameter	Value		Unit
$R_{thj-lead}$	Thermal resistance junction-lead (max)	15		°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient (max)	65 ⁽¹⁾	48 ⁽²⁾	°C/W

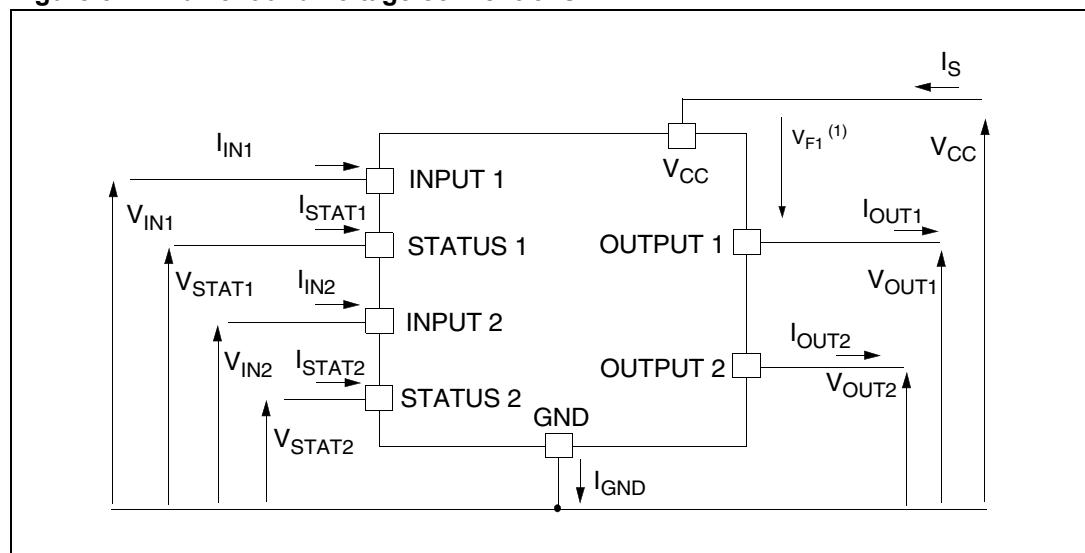
- When mounted on a standard single-sided FR-4 board with 0.5 cm² of Cu (at least 35 µm thick) connected to all V_{CC} pins. Horizontal mounting and no artificial air flow.
- When mounted on a standard single-sided FR-4 board with 6 cm² of Cu (at least 35 µm thick) connected to all V_{CC} pins. Horizontal mounting and no artificial air flow.

2.3 Electrical characteristics

Values specified in this section are for 8 V < V_{CC} < 36 V; -40 °C < T_j < 150 °C, unless otherwise stated.

(Per each channel)

Figure 3. Current and voltage conventions



- $V_{Fn} = V_{CCn} - V_{OUTn}$ during reverse battery condition.

Table 5. Power output

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{CC}^{(1)}$	Operating supply voltage		5.5	13	36	V
$V_{USD}^{(1)}$	Undervoltage shutdown		3	4	5.5	V
$V_{OV}^{(1)}$	Overvoltage shutdown		36			V
R_{ON}	On-state resistance	$I_{OUT} = 2\text{ A}$; $T_j = 25\text{ °C}$ $I_{OUT} = 2\text{ A}$; $V_{CC} > 8\text{ V}$			60 120	mΩ mΩ

Table 5. Power output (continued)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_S^{(1)}$	Supply current	Off-state; $V_{CC} = 13\text{ V}$; $V_{IN} = V_{OUT} = 0\text{ V}$		12	40	μA
		Off-state; $V_{CC} = 13\text{ V}$; $V_{IN} = V_{OUT} = 0\text{ V}$; $T_j = 25^\circ\text{C}$		12	25	μA
		On-state; $V_{CC} = 13\text{ V}$; $V_{IN} = 5\text{ V}$; $I_{OUT} = 0\text{ A}$		5	7	mA
$I_{L(off1)}$	Off-state output current	$V_{IN} = V_{OUT} = 0\text{ V}$	0		50	μA
$I_{L(off2)}$	Off-state output current	$V_{IN} = 0\text{ V}$; $V_{OUT} = 3.5\text{ V}$	-75		0	μA
$I_{L(off3)}$	Off-state output current	$V_{IN} = V_{OUT} = 0\text{ V}$; $V_{CC} = 13\text{ V}$; $T_j = 125^\circ\text{C}$			5	μA
$I_{L(off4)}$	Off-state output current	$V_{IN} = V_{OUT} = 0\text{ V}$; $V_{CC} = 13\text{ V}$; $T_j = 25^\circ\text{C}$			3	μA

1. Per device.

Table 6. Protections⁽¹⁾

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
T_{TSD}	Shutdown temperature		150	175	200	$^\circ\text{C}$
T_R	Reset temperature		135			$^\circ\text{C}$
T_{hyst}	Thermal hysteresis		7	15		$^\circ\text{C}$
T_{SDL}	Status delay in overload conditions	$T_j > T_{TSD}$			20	μs
I_{lim}	Current limitation	$V_{CC} = 13\text{ V}$	6	9	15	A
		$5.5\text{ V} < V_{CC} < 36\text{ V}$			15	A
V_{demag}	Turn-off output clamp voltage	$I_{OUT} = 2\text{ A}$; $L = 6\text{ mH}$	$V_{CC} - 41$	$V_{CC} - 48$	$V_{CC} - 55$	V

1. To ensure long term reliability under heavy overload or short circuit conditions, protection and related diagnostic signals must be used together with a proper software strategy. If the device is subjected to abnormal conditions, this software must limit the duration and number of activation cycles.

Table 7. V_{CC} - output diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_F	Forward on voltage	$-I_{OUT} = 1.3\text{ A}$; $T_j = 150^\circ\text{C}$	-	-	0.6	V

Table 8. Status pin

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{STAT}	Status low output voltage	$I_{STAT} = 1.6\text{ mA}$			0.5	V
I_{LSTAT}	Status leakage current	Normal operation; $V_{STAT} = 5\text{ V}$			10	μA
C_{STAT}	Status pin input capacitance	Normal operation; $V_{STAT} = 5\text{ V}$			100	pF

Table 8. Status pin (continued)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V _{SCL}	Status clamp voltage	I _{STAT} = 1 mA	6	6.8	8	V
		I _{STAT} = - 1 mA		-0.7		V

Table 9. Switching (V_{CC} = 13 V)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t _{d(on)}	Turn-on delay time	R _L = 6.5 Ω from V _{IN} rising edge to V _{OUT} = 1.3 V	-	30	-	μs
t _{d(off)}	Turn-off delay time	R _L = 6.5 Ω from V _{IN} falling edge to V _{OUT} = 11.7 V	-	30	-	μs
dV/dt _(on)	Turn-on voltage slope	R _L = 6.5 Ω from V _{OUT} = 1.3 V to V _{OUT} = 10.4 V	-	See Figure 14	-	V/μs
dV/dt _(off)	Turn-off voltage slope	R _L = 6.5 Ω from V _{OUT} = 11.7 V to V _{OUT} = 1.3 V	-	See Figure 15	-	V/μs

Table 10. Open-load detection

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I _{OL}	Open-load on-state detection threshold	V _{IN} = 5 V	50	100	200	mA
t _{DOL(on)}	Open-load on-state detection delay	I _{OUT} = 0 A			200	μs
V _{OL}	Open-load off-state voltage detection threshold	V _{IN} = 0 V	1.5	2.5	3.5	V
t _{DOL(off)}	Open-load detection delay at turn-off				1000	μs

Table 11. Logic input

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V _{IL}	Input low level				1.25	V
I _{IL}	Low level input current	V _{IN} = 1.25 V	1			μA
V _{IH}	Input high level		3.25			V
I _{IH}	High level input current	V _{IN} = 3.25 V			10	μA
V _{hyst}	Input hysteresis voltage		0.5			V
V _{ICL}	Input clamp voltage	I _{IN} = 1 mA	6	6.8	8	V
		I _{IN} = -1 mA		-0.7		V

Figure 4. Switching time waveforms

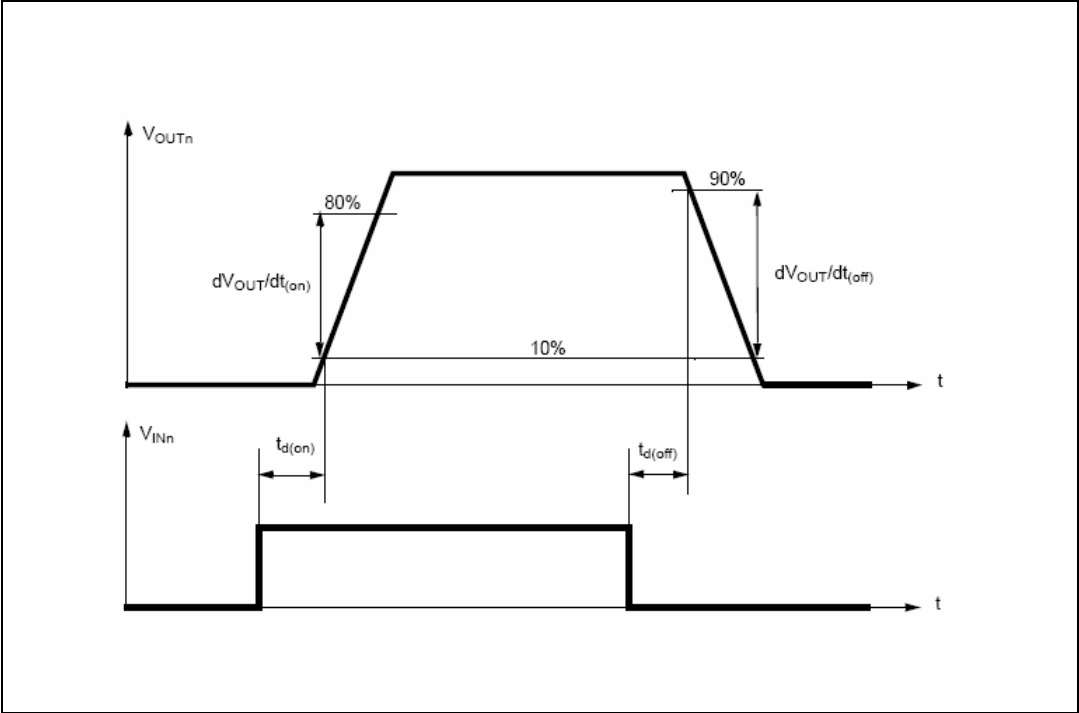


Table 12. Truth table

Conditions	Input	Output	Sense
Normal operation	L	L	H
	H	H	H
Current limitation	L	L	H
	H	X	$(T_j < T_{TSD})$ H $(T_j > T_{TSD})$ L
Overtemperature	L	L	H
	H	L	L
Undervoltage	L	L	X
	H	L	X
Overvoltage	L	L	H
	H	L	H
Output voltage > V_{OL}	L	H	L
	H	H	H
Output current < I_{OL}	L	L	H
	H	H	L

Table 13. Electrical transient requirements on V_{CC} pin (part 1)

ISO T/R 7637/1 test pulse	Test levels				
	I	II	III	IV	Delays and impedance
1	-25 V	-50 V	-75 V	-100 V	2 ms, 10 Ω
2	+25 V	+50 V	+75 V	+100 V	0.2 ms, 10 Ω
3a	-25 V	-50 V	-100 V	-150 V	0.1 μs, 50 Ω
3b	+25 V	+50 V	+75 V	+100 V	0.1 μs, 50 Ω
4	-4 V	-5 V	-6 V	-7 V	100 ms, 0.01 Ω
5	+26.5 V	+46.5 V	+66.5 V	+86.5 V	400 ms, 2 Ω

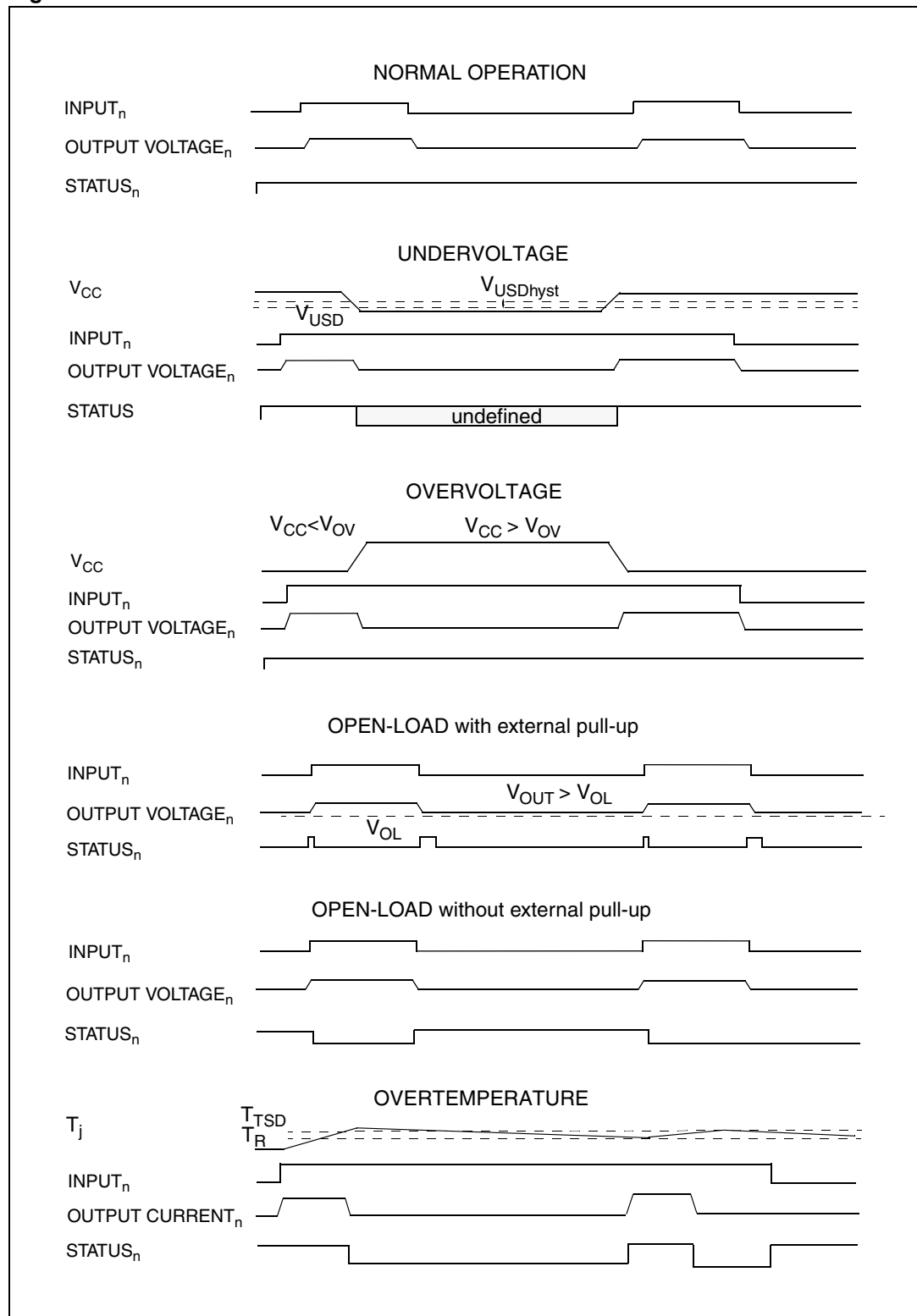
Table 14. Electrical transient requirements on V_{CC} pin (part 2)

ISO T/R 7637/1 test pulse	Test levels results			
	I	II	III	IV
1	C	C	C	C
2	C	C	C	C
3a	C	C	C	C
3b	C	C	C	C
4	C	C	C	C
5	C	E	E	E

Table 15. Electrical transient requirements on V_{CC} pin (part 3)

Class	Contents
C	All functions of the device are performed as designed after exposure to disturbance.
E	One or more functions of the device is not performed as designed after exposure to disturbance and cannot be returned to proper operation without replacing the device.

Figure 5. Waveforms



2.4 Electrical characteristics curves

Figure 6. Off-state output current

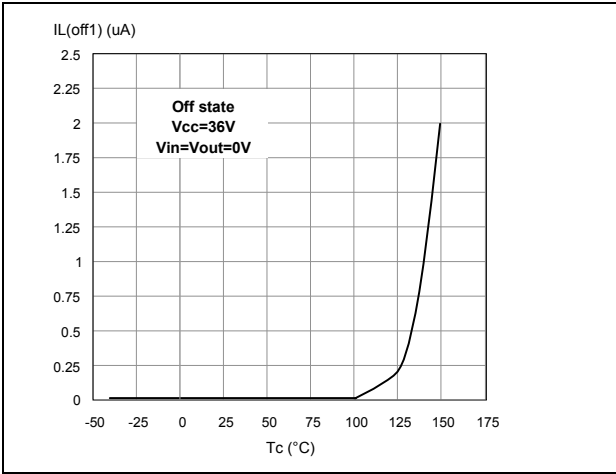


Figure 7. High level input current

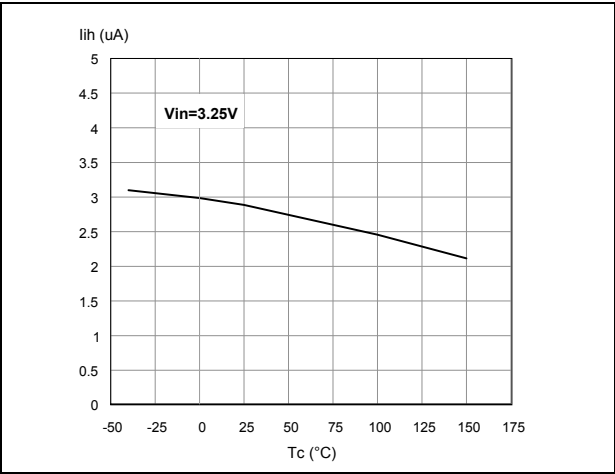


Figure 8. Input clamp voltage

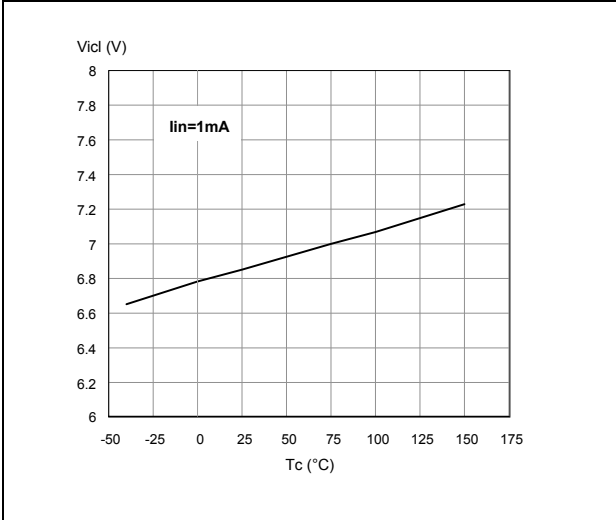


Figure 9. Status leakage current

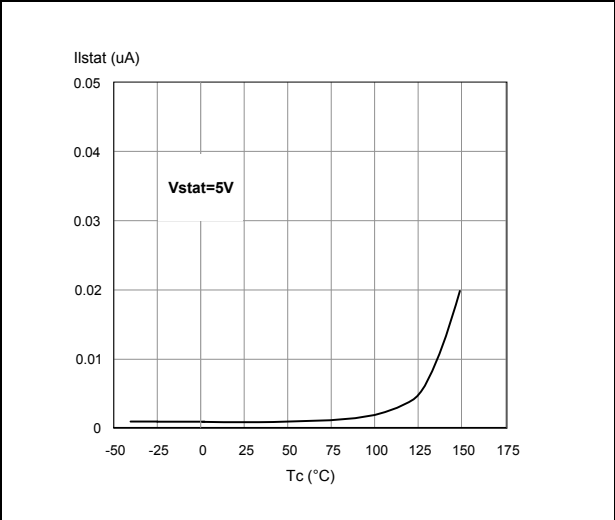


Figure 10. Status low output voltage

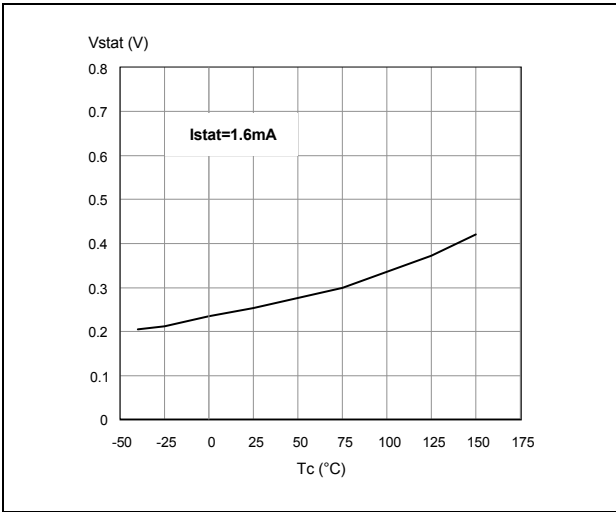


Figure 11. Status clamp voltage

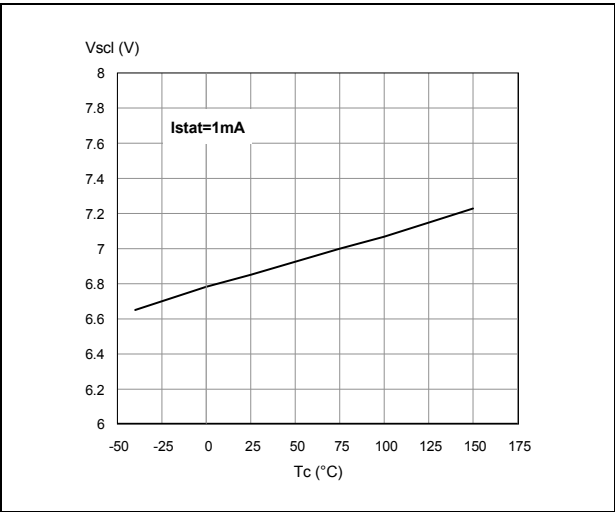


Figure 12. Overvoltage shutdown

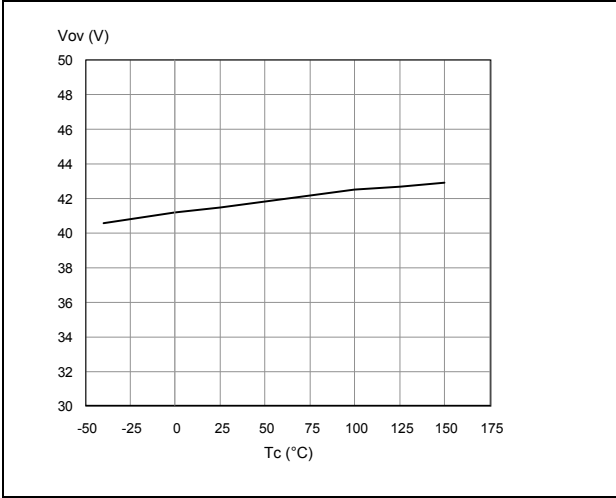


Figure 13. I_{LIM} vs T_{case}

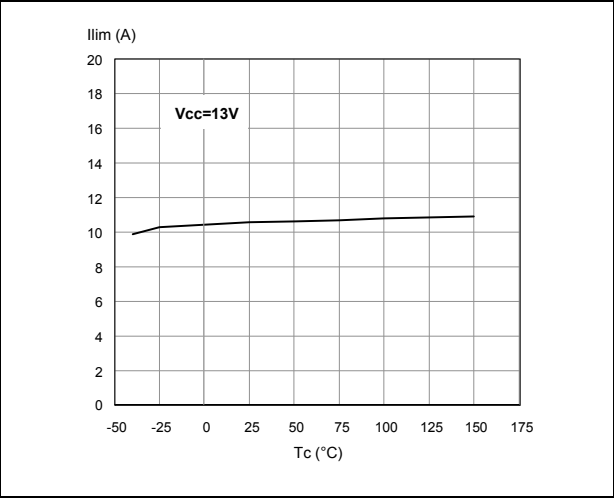


Figure 14. Turn-on voltage slope

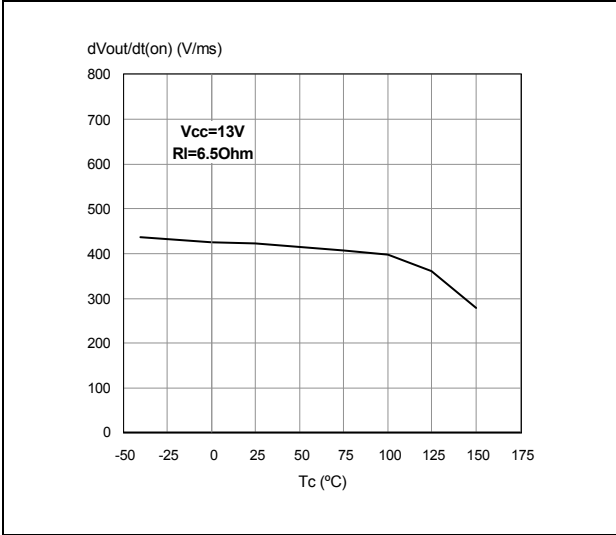


Figure 15. Turn-off voltage slope

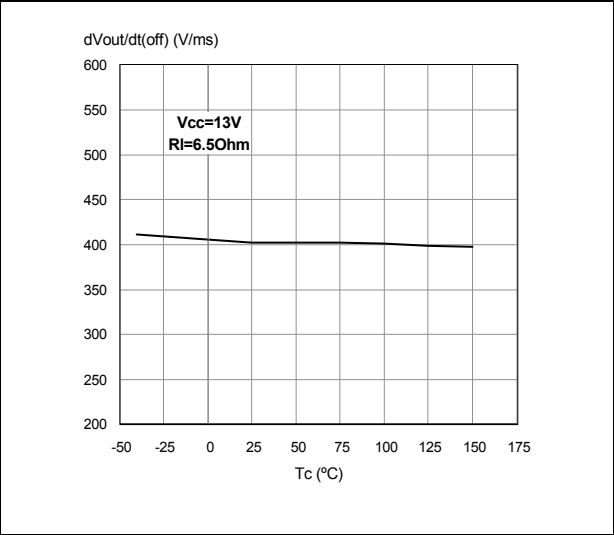


Figure 16. On-state resistance vs T_{case}

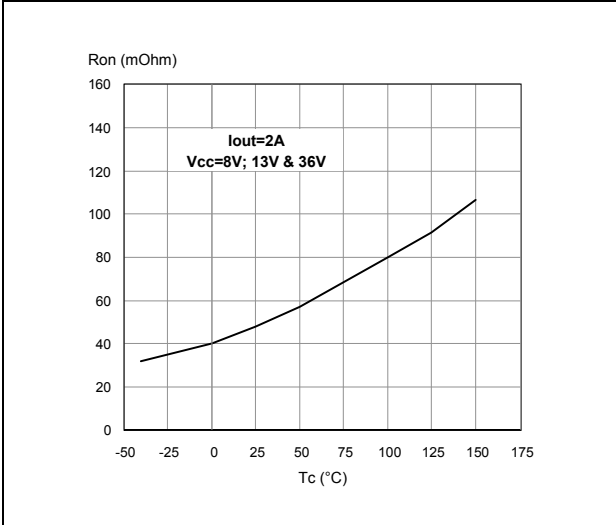


Figure 17. On-state resistance vs V_{cc}

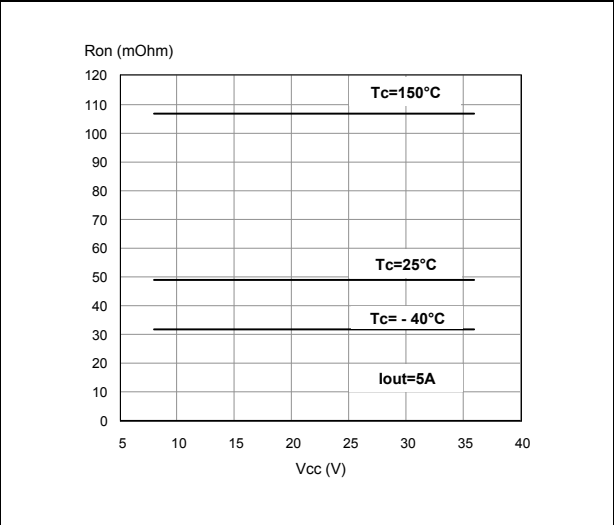


Figure 18. Input high level

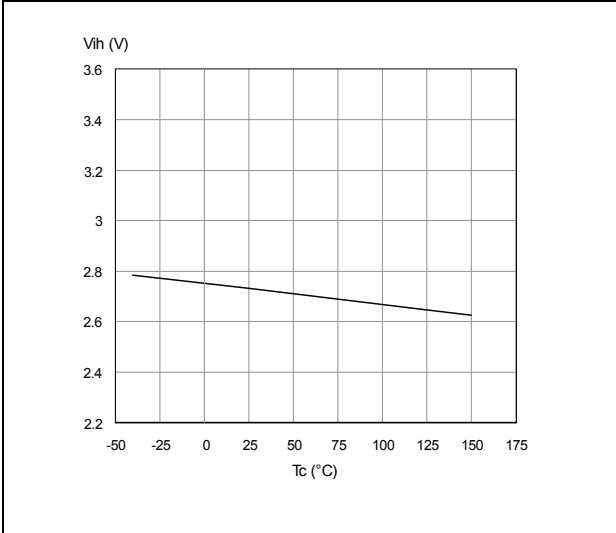


Figure 19. Input low level

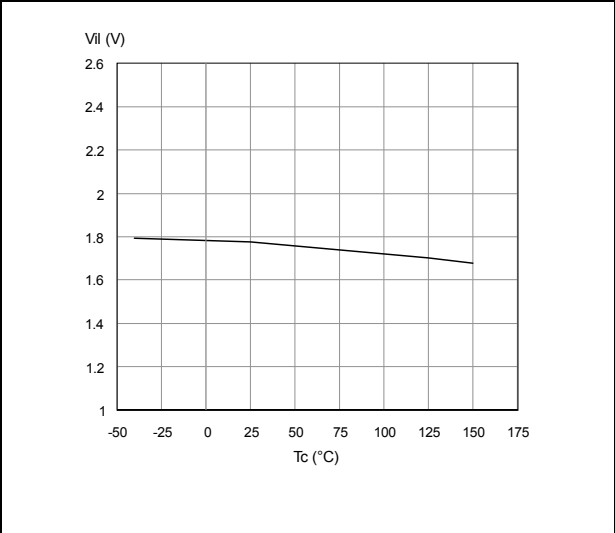


Figure 20. Open-load on-state detection threshold

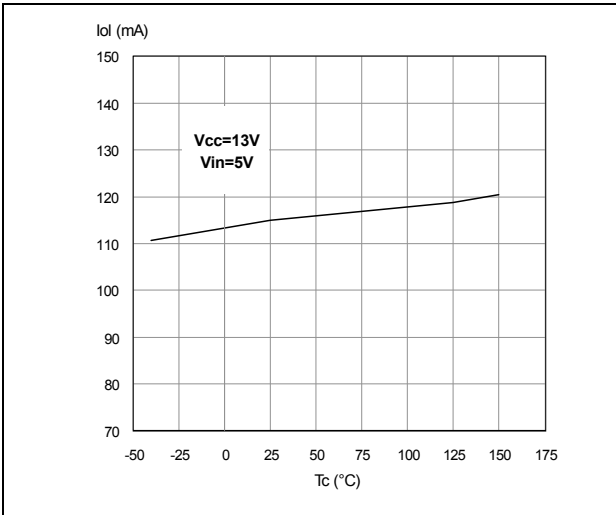


Figure 21. Open-load off-state detection threshold

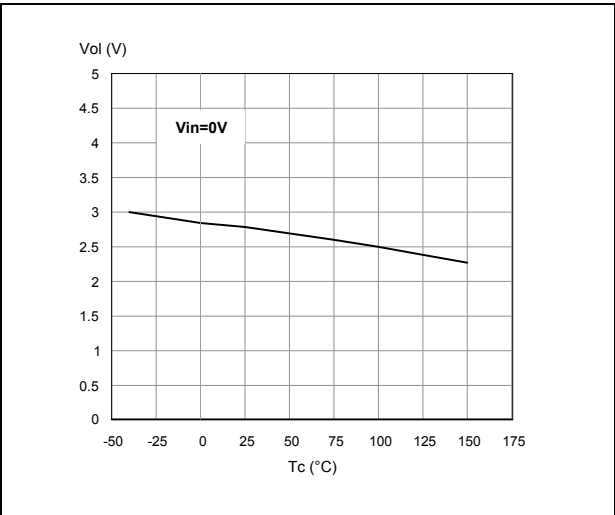
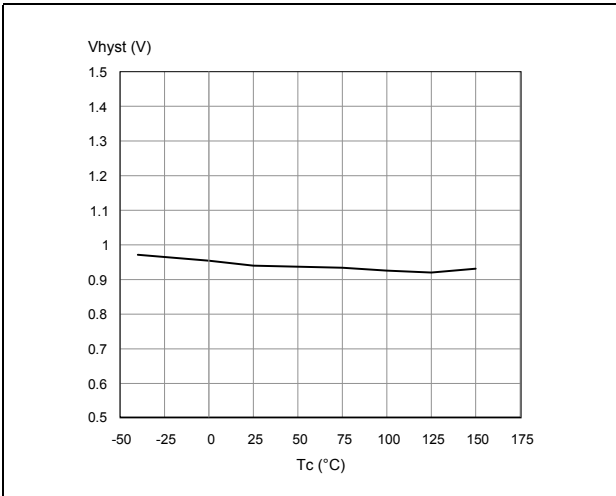
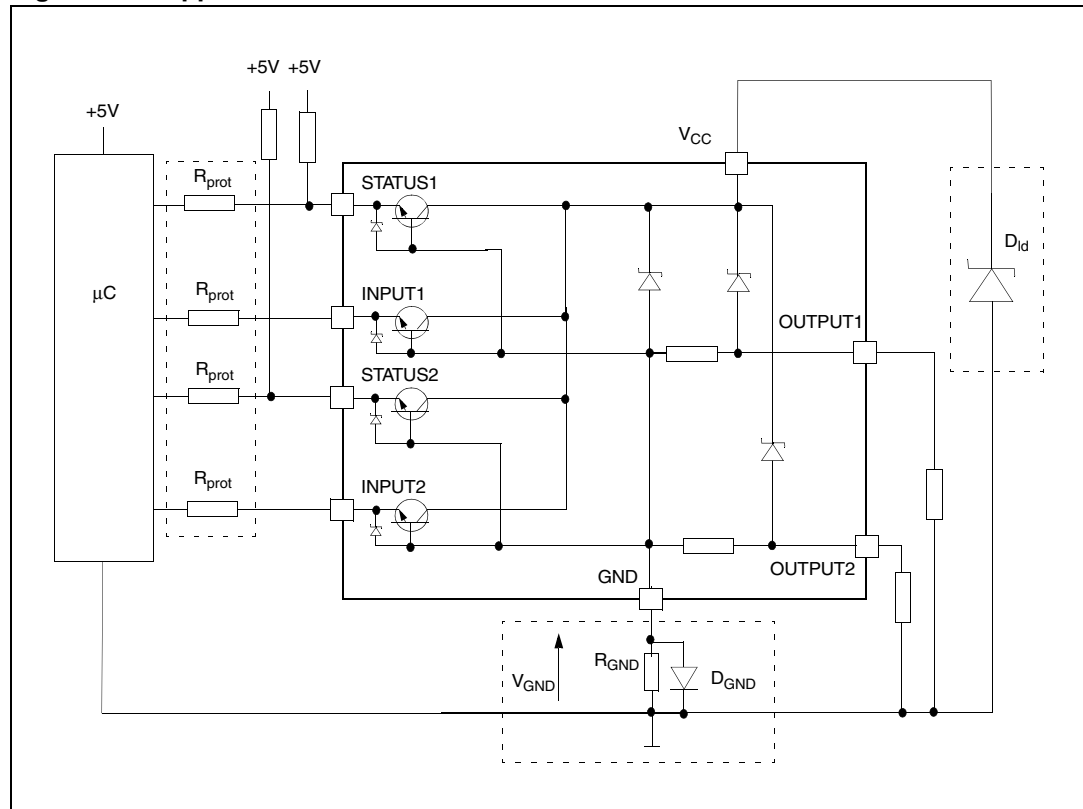


Figure 22. Input hysteresis voltage



3 Application information

Figure 23. Application schematic



3.1 GND protection network against reverse battery

This section provides two solutions for implementing a ground protection network against reverse battery.

3.1.1 Solution 1: a resistor in the ground line (R_{GND} only)

This can be used with any type of load.

The following shows how to dimension the R_{GND} resistor:

1. $R_{GND} \leq 600 \text{ mV} / (I_{S(on)max})$
2. $R_{GND} \geq (-V_{CC}) / (-I_{GND})$

where $-I_{GND}$ is the DC reverse ground pin current and can be found in the absolute maximum rating section of the device's datasheet.

Power dissipation in R_{GND} (when $V_{CC} < 0$ during reverse battery situations) is:

$$P_D = (-V_{CC})^2 / R_{GND}$$

This resistor can be shared amongst several different HSD. Please note that the value of this resistor should be calculated with formula (1) where $I_{S(on)max}$ becomes the sum of the maximum on-state currents of the different devices.

Please note that, if the microprocessor ground is not common with the device ground, then the R_{GND} produces a shift ($I_{S(on)max} * R_{GND}$) in the input thresholds and the status output values. This shift varies depending on how many devices are ON in the case of several high-side drivers sharing the same R_{GND} .

If the calculated power dissipation requires the use of a large resistor, or several devices have to share the same resistor, then ST suggests using [Section 3.1.2](#) described below.

3.1.2 Solution 2: a diode (D_{GND}) in the ground line

A resistor ($R_{GND} = 1\text{ k}\Omega$) should be inserted in parallel to D_{GND} if the device is driving an inductive load. This small signal diode can be safely shared amongst several different HSD. Also in this case, the presence of the ground network produce a shift ($\sim 600\text{ mV}$) in the input threshold and the status output values if the microprocessor ground is not common with the device ground. This shift does not vary if more than one HSD shares the same diode/resistor network. Series resistor in INPUT and STATUS lines are also required to prevent that, during battery voltage transient, the current exceeds the absolute maximum rating. Safest configuration for unused INPUT and STATUS pin is to leave them unconnected.

3.2 Load dump protection

D_{ld} is necessary (Voltage Transient Suppressor) if the load dump peak voltage exceeds the V_{CC} maximum DC rating. The same applies if the device is subjected to transients on the V_{CC} line that are greater than those shown in [Table 13](#).

3.3 MCU I/O protection

If a ground protection network is used and negative transients are present on the V_{CC} line, the control pins are pulled negative. ST suggests to insert a resistor (R_{prot}) in line to prevent the microcontroller I/O pins from latching up.

The value of these resistors is a compromise between the leakage current of microcontroller and the current required by the HSD I/Os (Input levels compatibility) with the latch-up limit of microcontroller I/Os:

$$-V_{CCpeak} / I_{latchup} \leq R_{prot} \leq (V_{OH\mu C} - V_{IH} - V_{GND}) / I_{IHmax}$$

Example

For the following conditions:

$$V_{CCpeak} = -100\text{ V}$$

$$I_{latchup} \geq 20\text{ mA}$$

$$V_{OH\mu C} \geq 4.5\text{ V}$$

$$5\text{ k}\Omega \leq R_{prot} \leq 65\text{ k}\Omega$$

The recommended values are:

$$R_{prot} = 10\text{ k}\Omega$$

3.4 Open-load detection in off-state

Off-state open-load detection requires an external pull-up resistor (R_{PU}) connected between OUTPUT pin and a positive supply voltage (V_{PU}) like the +5 V line used to supply the microprocessor.

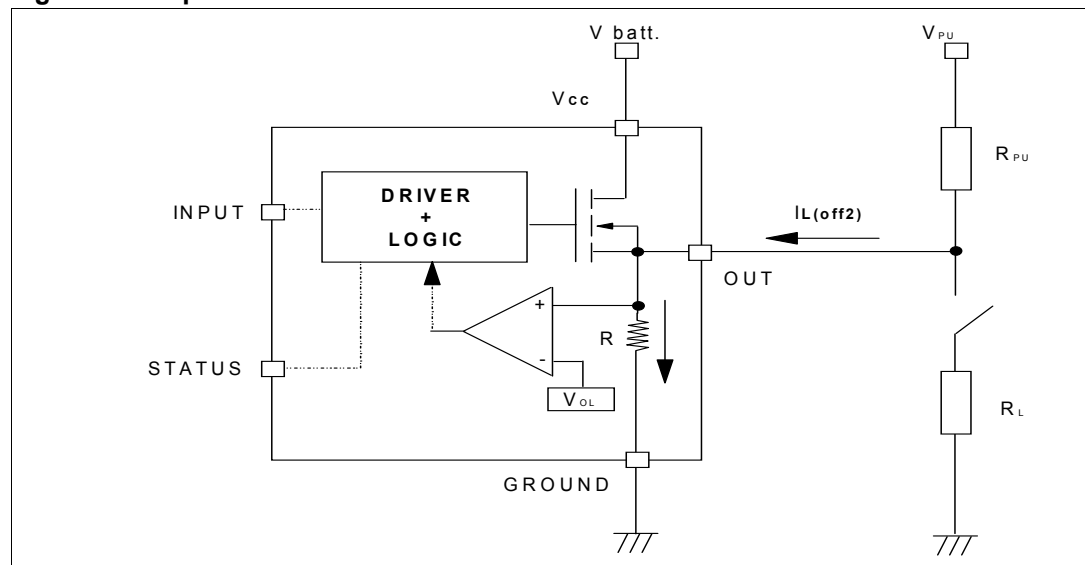
The external resistor has to be selected according to the following requirements:

1. No false open-load indication when load is connected: in this case it needs to avoid V_{OUT} to be higher than V_{OLmin} ; this results in the following condition $V_{OUT} = (V_{PU} / (R_L + R_{PU}))R_L < V_{OLmin}$.
2. No misdetection when load is disconnected: in this case the V_{OUT} has to be higher than V_{OLmax} ; this results in the following condition $R_{PU} < (V_{PU} - V_{OLmax}) / I_{L(off2)}$.

Because $I_{S(OFF)}$ may significantly increase if V_{out} is pulled high (up to several mA), the pull-up resistor R_{PU} should be connected to a supply that is switched OFF when the module is in standby.

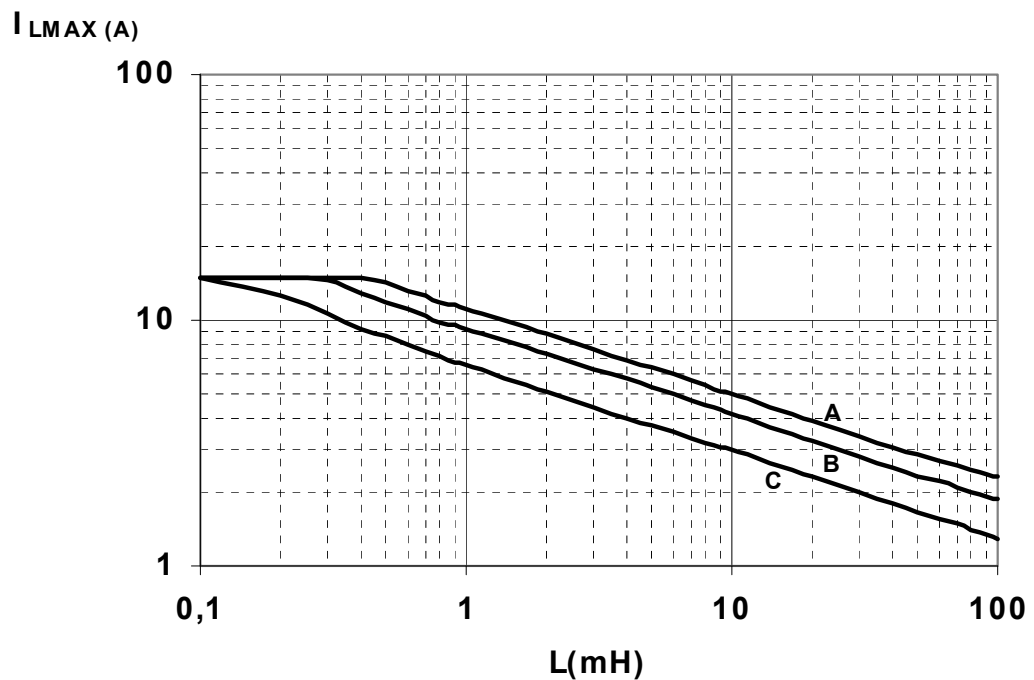
The values of V_{OLmin} , V_{OLmax} and $I_{L(off2)}$ are available in [Chapter 2: Electrical specifications](#).

Figure 24. Open-load detection in off-state



3.5 Maximum demagnetization energy

Figure 25. SO-16L maximum turn-off current versus load inductance



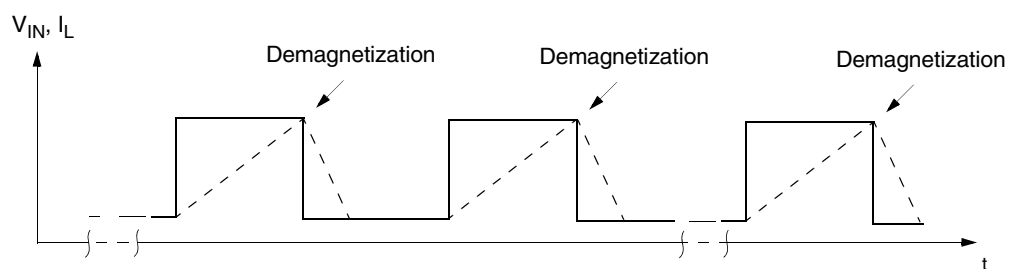
A = single pulse at $T_{Jstart} = 150\text{ }^{\circ}\text{C}$

B = repetitive pulse at $T_{Jstart} = 100\text{ }^{\circ}\text{C}$

C = repetitive pulse at $T_{Jstart} = 125\text{ }^{\circ}\text{C}$

Conditions:

$V_{CC} = 13.5\text{ V}$



Note:

Values are generated with $R_L = 0\text{ }\Omega$.

In case of repetitive pulses, T_{Jstart} (at beginning of each demagnetization) of every pulse must not exceed the temperature specified above for curves B and C.

4 Package and PCB thermal data

4.1 SO-16L thermal data

Figure 26. SO-16L PC board⁽¹⁾

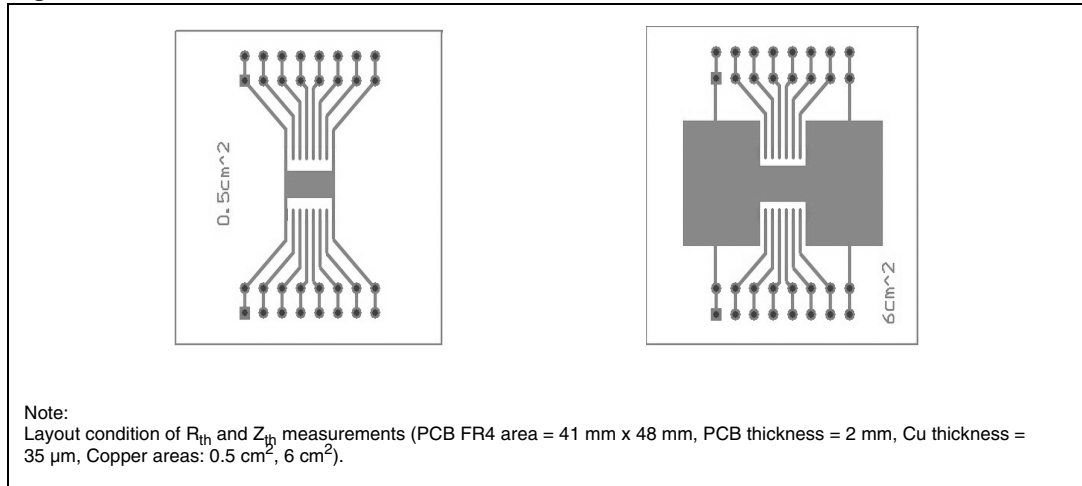


Figure 27. $R_{thj-amb}$ vs PCB copper area in open box free air condition

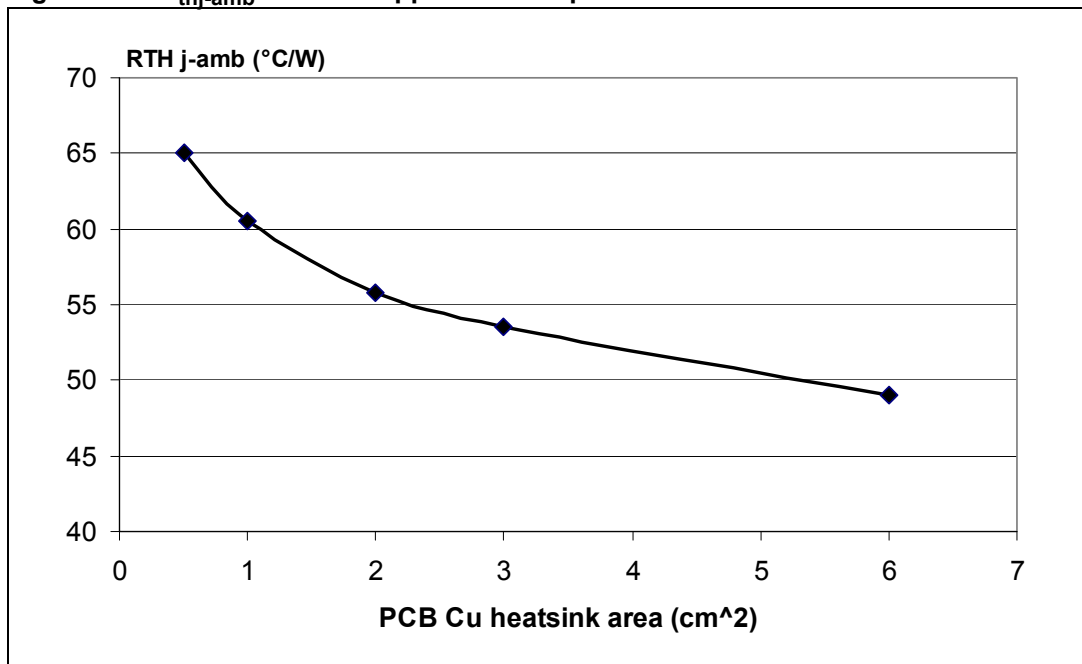
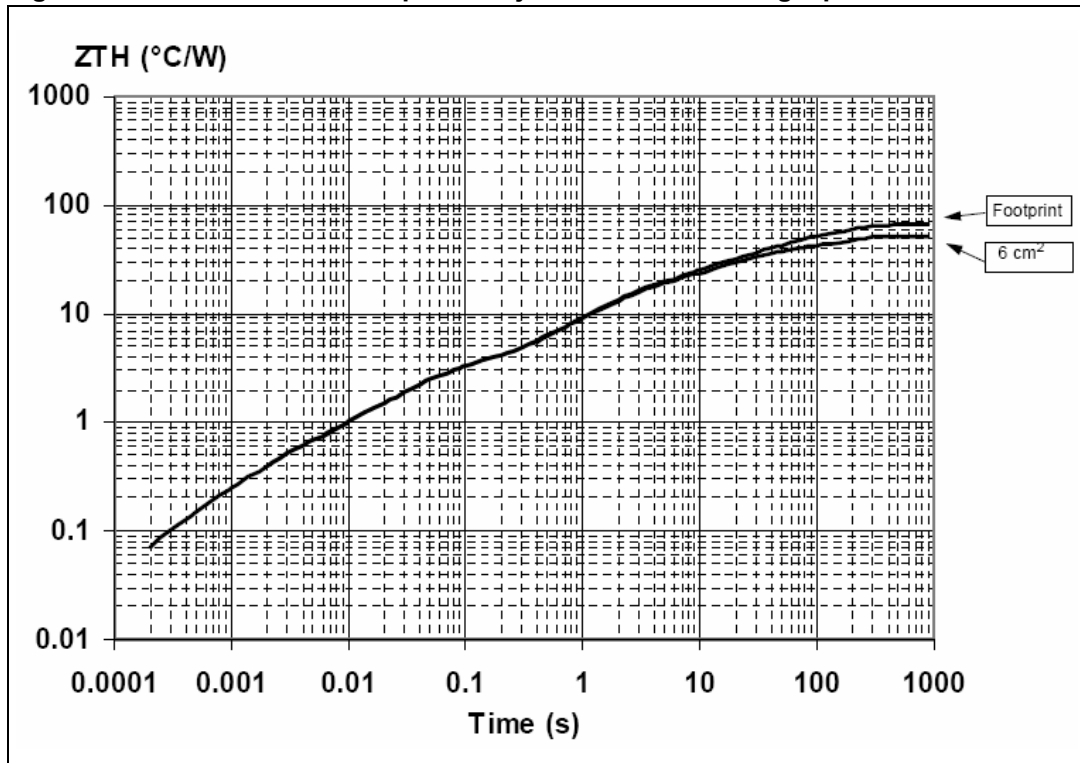


Figure 28. SO-16 L thermal impedance junction ambient single pulse



Equation 1: pulse calculation formula

$$Z_{TH\delta} = R_{TH} \cdot \delta + Z_{THtp}(1 - \delta)$$

$$\text{where } \delta = t_p / T$$

Figure 29. Thermal fitting model of a quad channel HSD in SO-16L

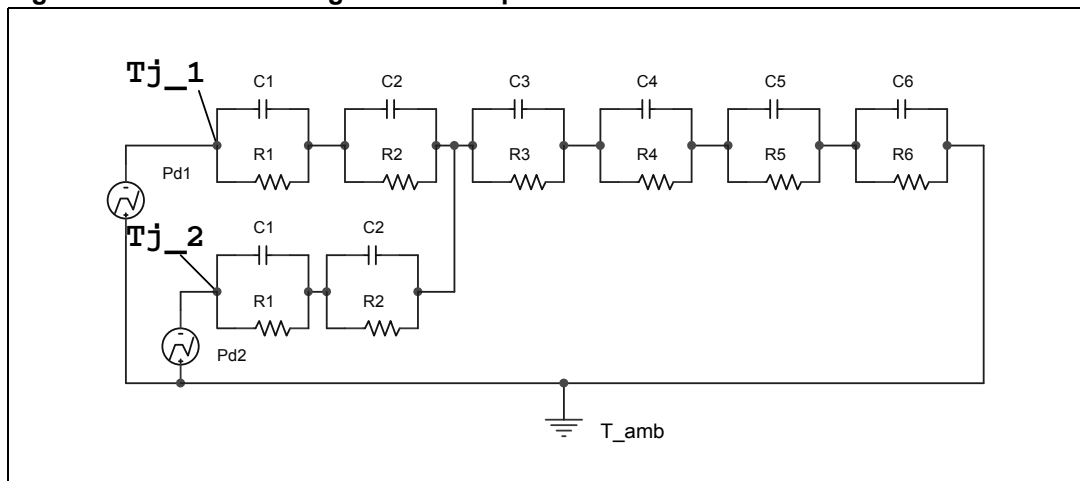


Table 16. Thermal parameters

Area/ island (cm ²)	Footprint	6
R1 (°C/W)	0.05	
R2 (°C/W)	0.3	
R3 (°C/W)	2.2	
R4 (°C/W)	12	
R5 (°C/W)	15	
R6 (°C/W)	37	22
C1 (W.s/°C)	0.001	
C2 (W.s/°C)	5.00E-03	
C3 (W.s/°C)	0.02	
C4 (W.s/°C)	0.3	
C5 (W.s/°C)	1	
C6 (W.s/°C)	3	5

5 Package and packing information

5.1 ECOPACK® packages

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

5.2 SO-16L package information

Figure 30. SO-16L package dimensions

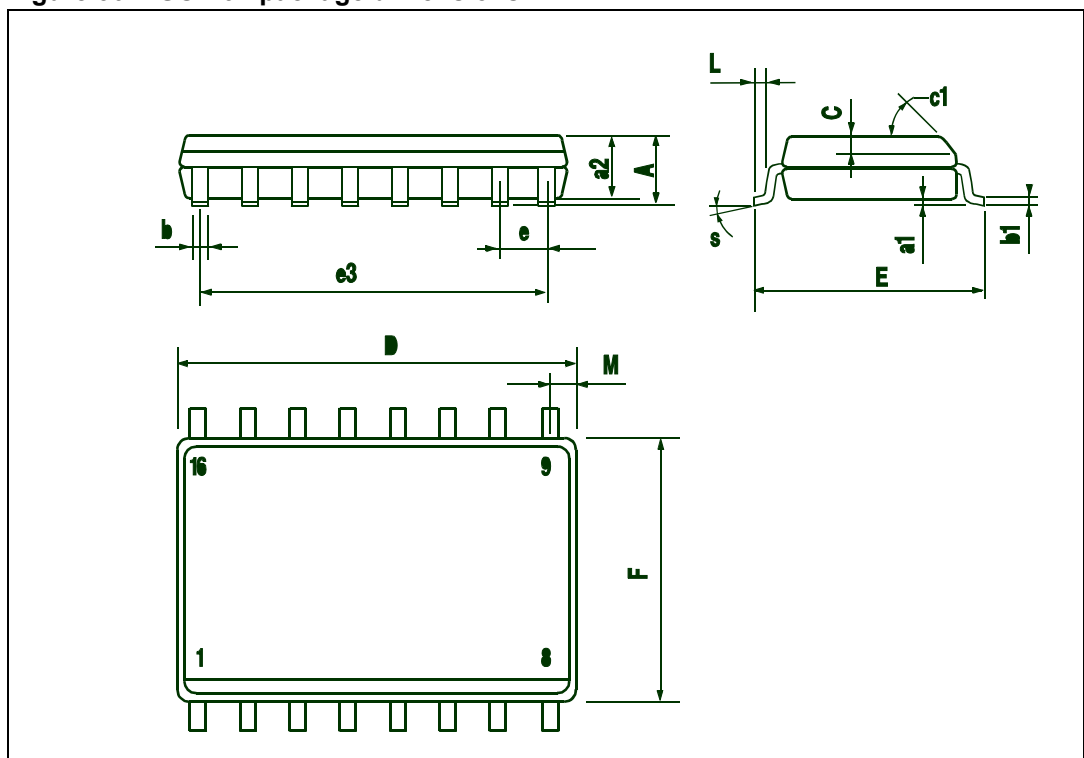


Table 17. SO-16L mechanical data

DIM.	mm.		
	Min.	Typ.	Max.
A			2.65
a1	0.1		0.2
a2			2.45
b	0.35		0.49
b1	0.23		0.32
C		0.5	
c1	45° (typ.)		
D	10.1		10.5
E	10.0		10.65
e		1.27	
e3		8.89	
F	7.4		7.6
L	0.5		1.27
M			0.75
S	8° (max.)		

5.3 SO-16L packing information

Figure 31. SO-16L tube shipment (no suffix)

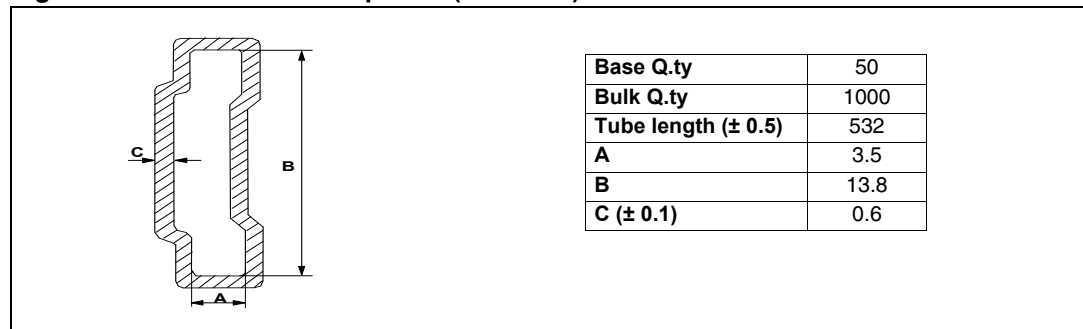
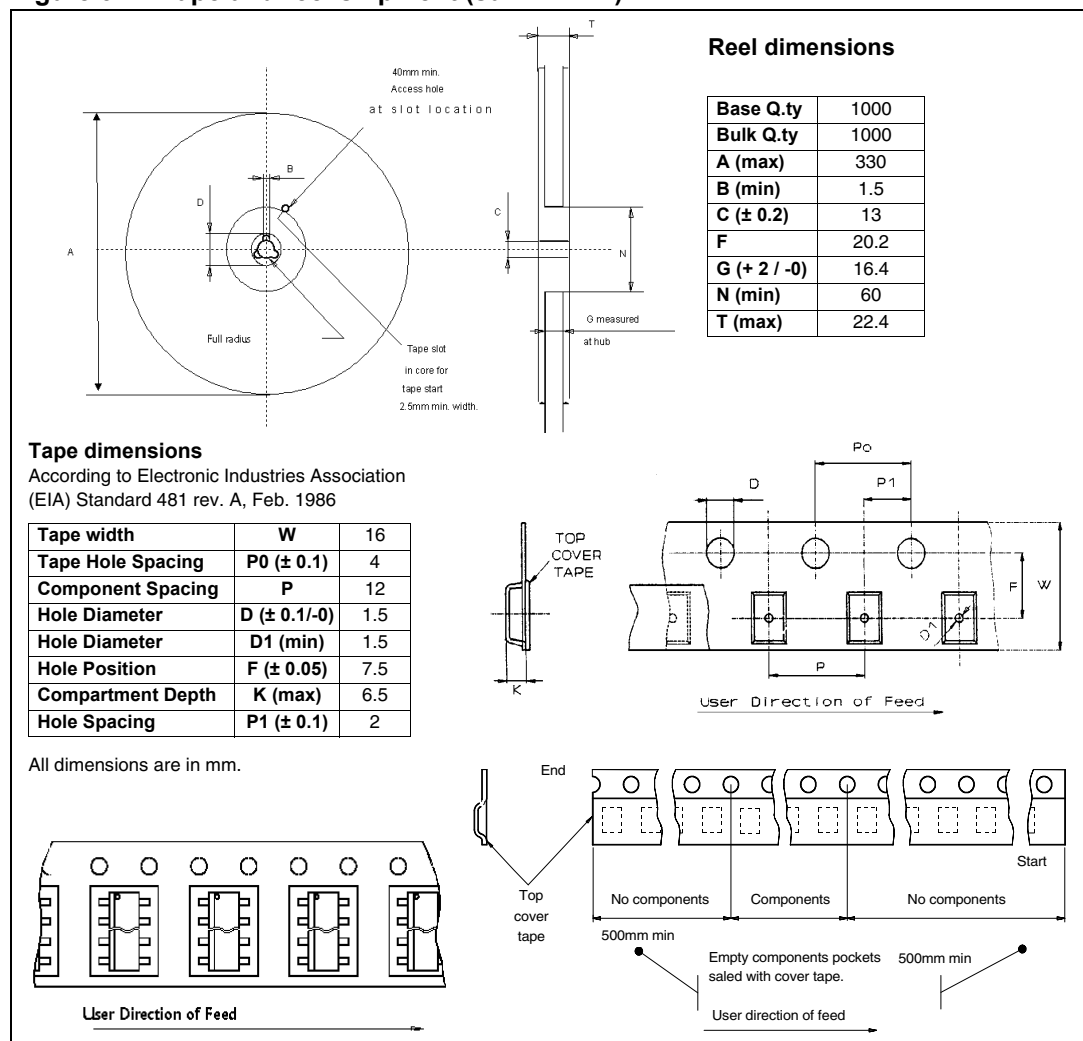


Figure 32. Tape and reel shipment (suffix “TR”)



6 Revision history

Table 18. Document revision history

Date	Revision	Changes
25-May-2010	1	Initial release.
22-Sep-2010	2	Changed document status from preliminary data to datasheet.
19-Sep-2013	3	Updated Disclaimer

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